ToF-SIMS depth profiling of PS-*b*-PMMA block copolymers using Ar_n^+, C_{60}^{++} and Cs^+ sputtering ions

Supporting Information

T. Terlier[a,c], G. Zappalà[b], C. Marie[a], D. Leonard[c], J-P. Barnes[a*] and A. Licciardello[b]

[a]: University Grenoble Alpes, F-38000 Grenoble, France
CEA, LETI, MINATEC Campus, F-38054 Grenoble, France.
[b]: Dipartimento di Scienze Chimiche, Università degli Studi di Catania and CSGI,
Viale A. Doria 6, 95125 Catania, Italy.
[c]: Univ Lyon, CNRS, Université Claude Bernard Lyon 1, ENS de Lyon, Institut des Sciences Analytiques, UMR 5280, 5, rue de la Doua, F-69100 Villeurbanne, France.

*Email: jean-paul.barnes@cea.fr

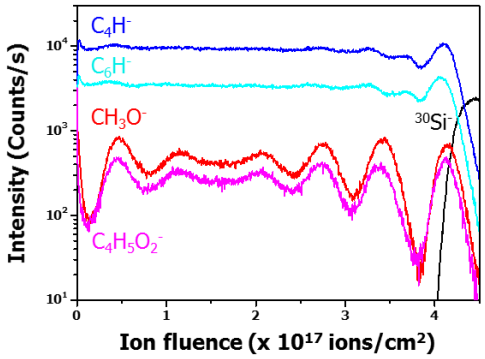

Figure S1. *Negative ion ToF-SIMS depth profile obtained with 250 eV Cs^+ ion sputtering of a 220 nm PS-b-PMMA layer at 70/30 wt.% annealed (theoretically organized in cylindrical blocks), deposited on a silicon substrate.*

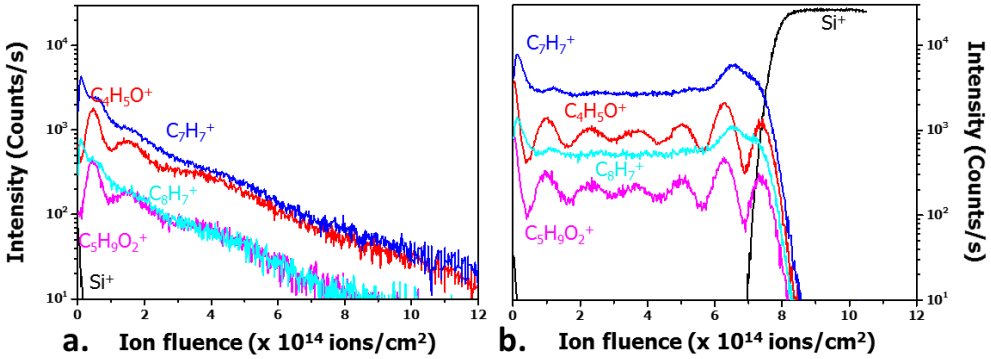

Figure S2. *Positive ion ToF-SIMS depth profile obtained with C_{60}^{++} ion sputtering, respectively, (a) without NO gas dosing and at room temperature (293 K) and (b) with NO gas dosing and at 150 K, of a 220 nm thick annealed PS-b-PMMA layer at 70/30 wt.% (theoretically organized in cylindrical blocks), deposited on a silicon substrate.*

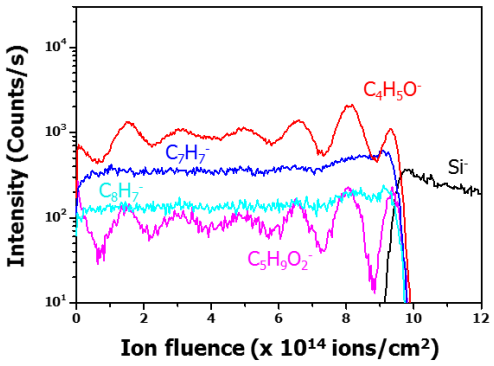

Figure S3. *Negative ion ToF-SIMS depth profile obtained with Ar_{1500}^+ ion sputtering at 5 keV of a 220 nm thick annealed PS-b-PMMA layer at 70/30 wt.% (theoretically organized in cylindrical blocks), deposited on a silicon substrate.*